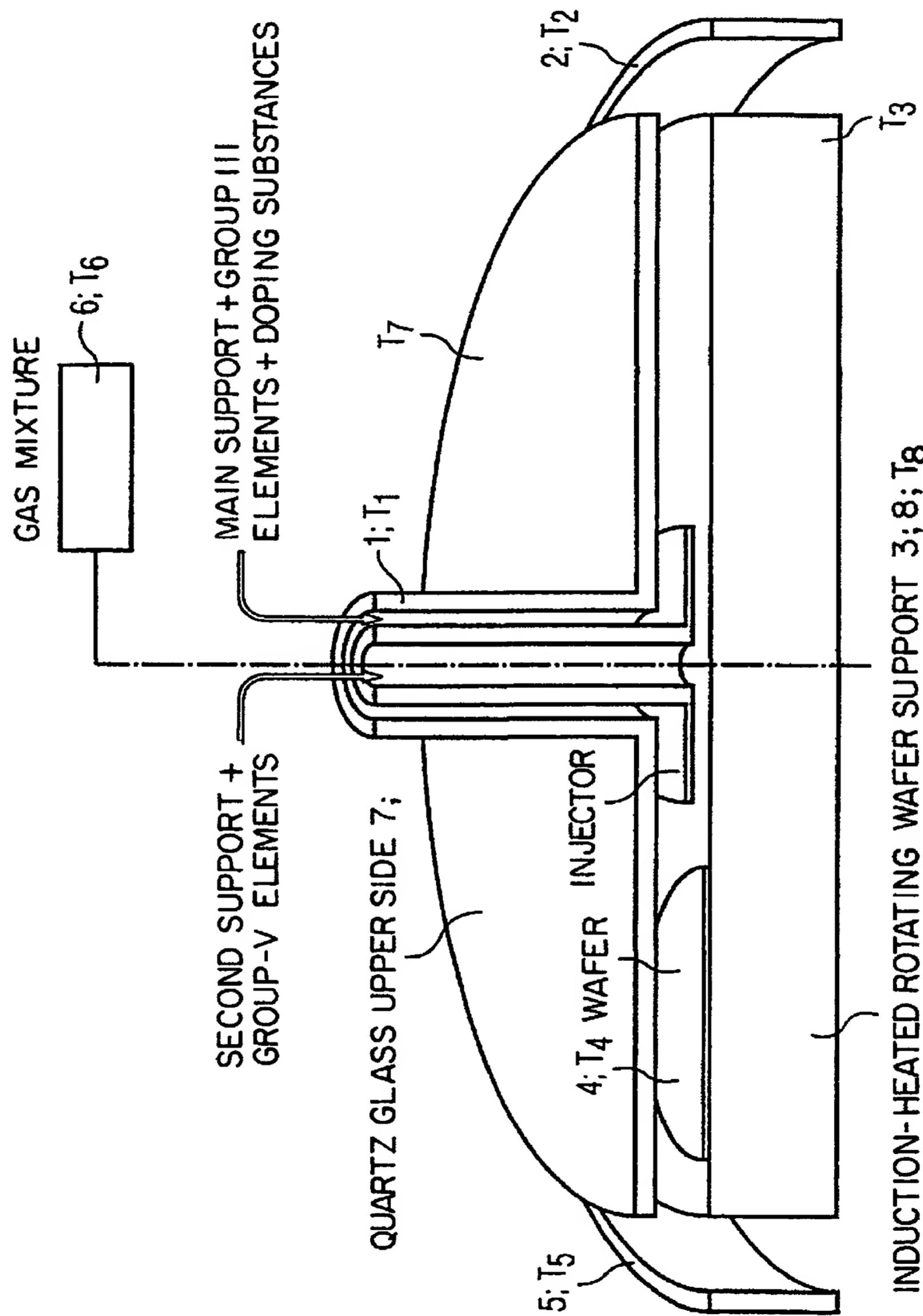




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*FIG. 1*

IN FRACTION AS A FUNCTION OF  
THE PRODUCTION TEMPERATURE

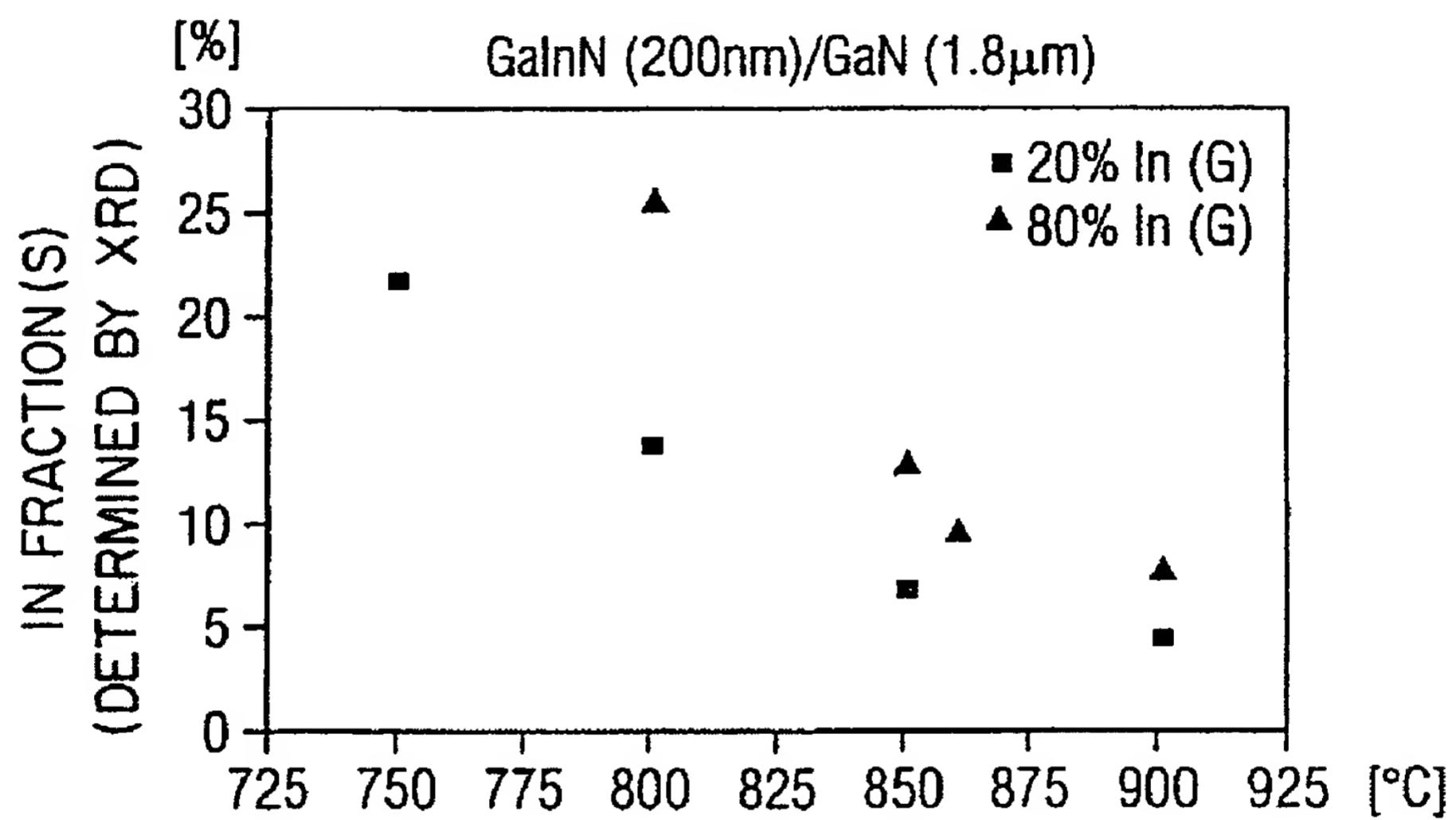


FIG. 2

LOG DATA OF THE AIXTRON MOVPE SYSTEM  
InGaN/GaN DH STRUCTURE

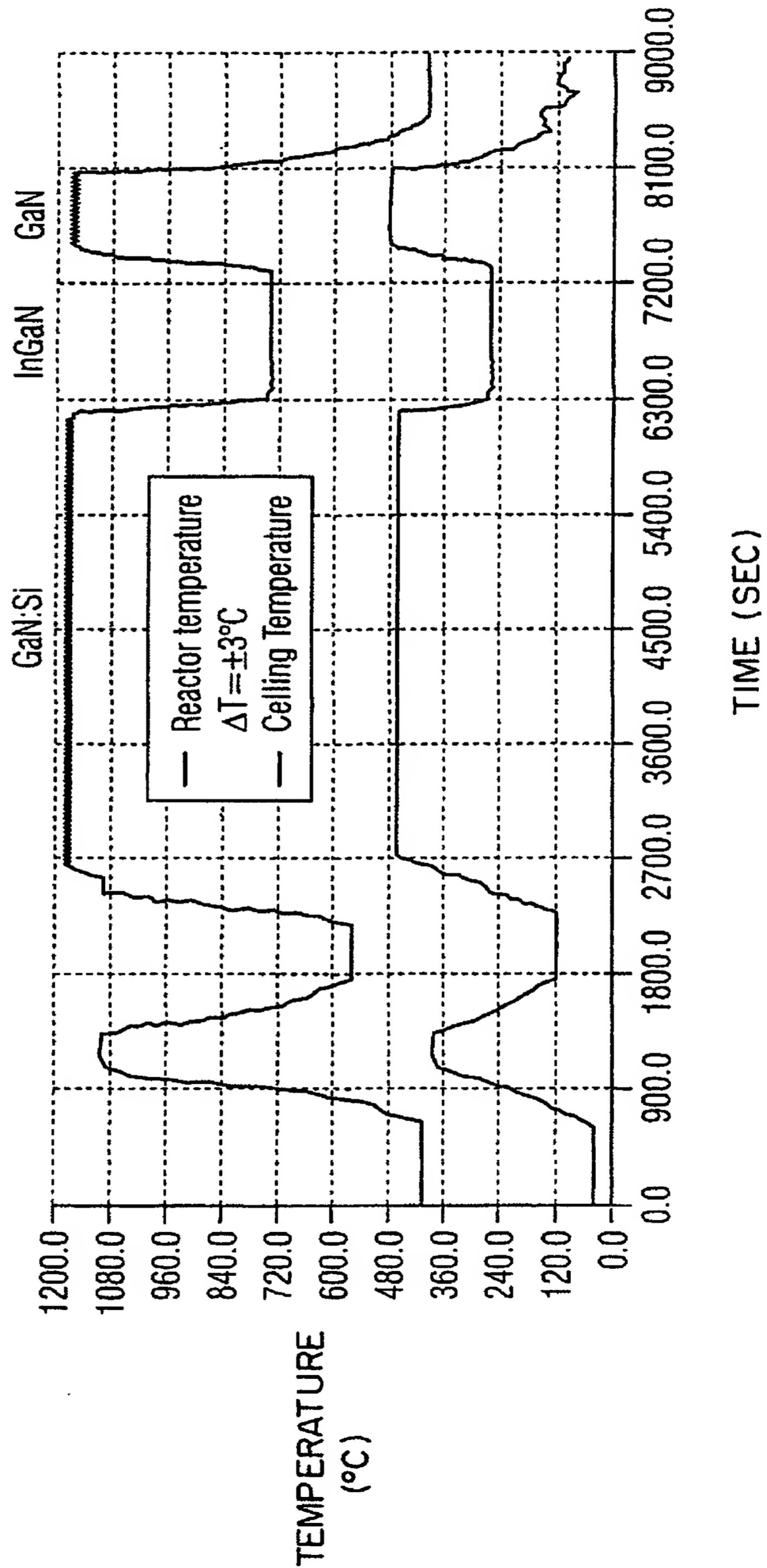


FIG. 3

MASS TRANSFER MODEL  
SCHEMATIC ILLUSTRATION THE COMPUTING RANGE AND THE  
FINITE VOLUME LATTICE FOR ANALYZING THE MASS TRANSFER

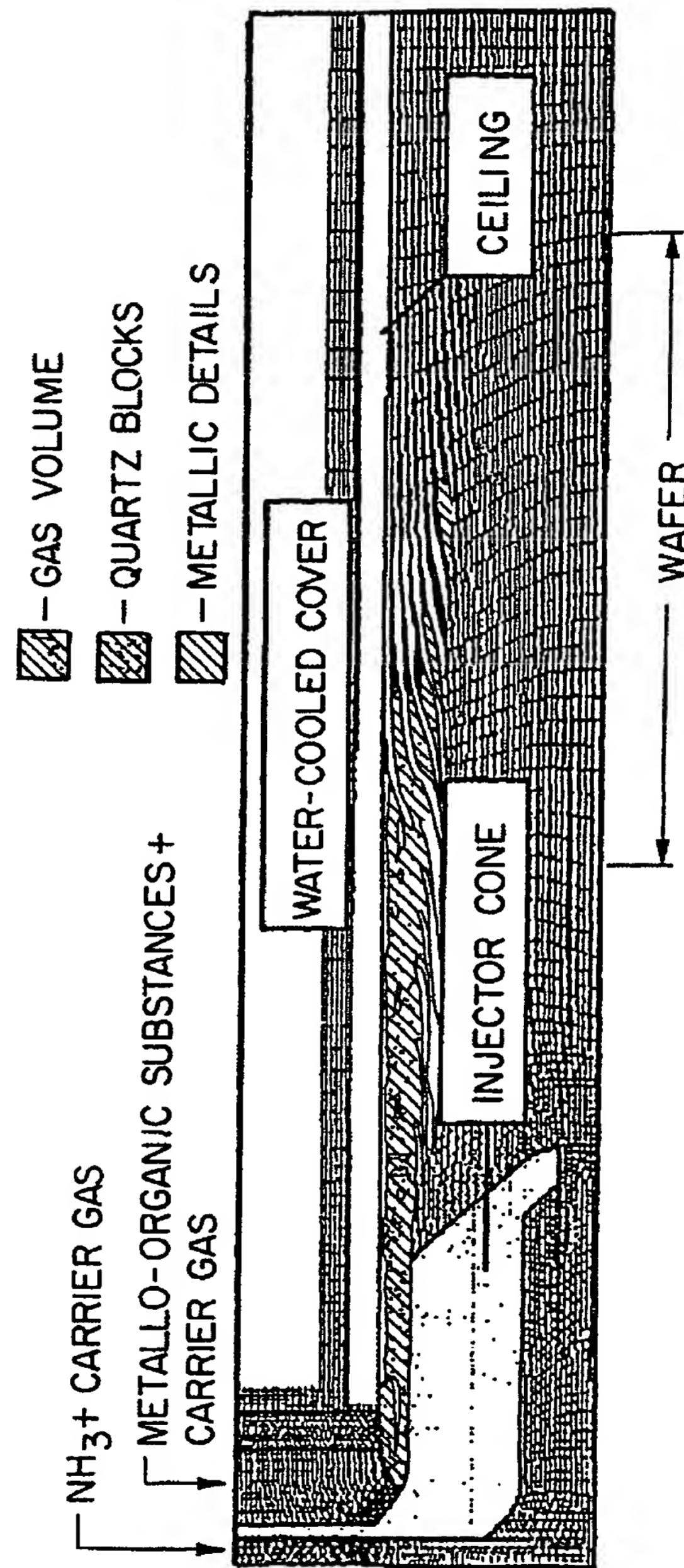


FIG. 3a

THE MODEL EXPLAINS:

- MIXTURE AND REACTION OF PRECURSOR FLOWS
- GREY DIFFUSE RADIATION
- CONJUGATED HEAT TRANSMISSION

TEMPERATURE DISTRIBUTION

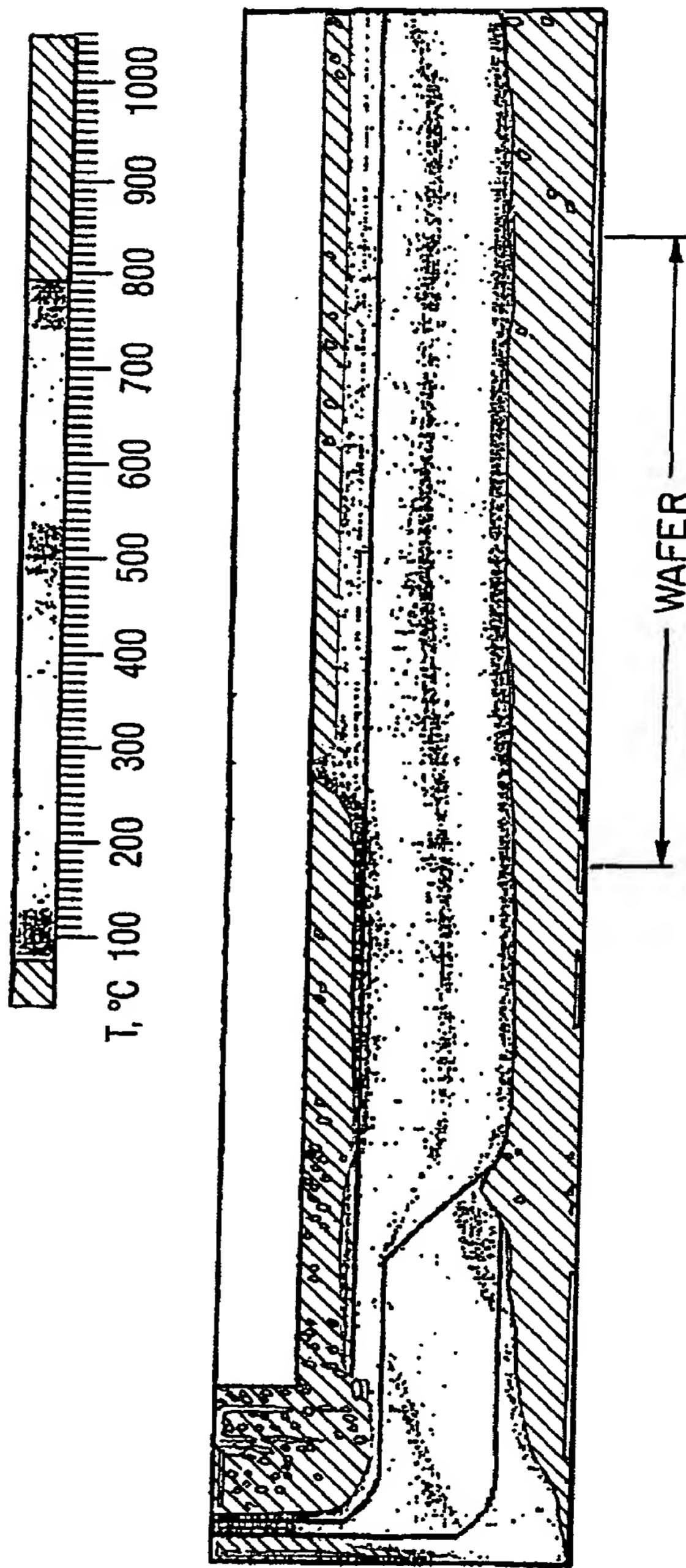


FIG. 3b

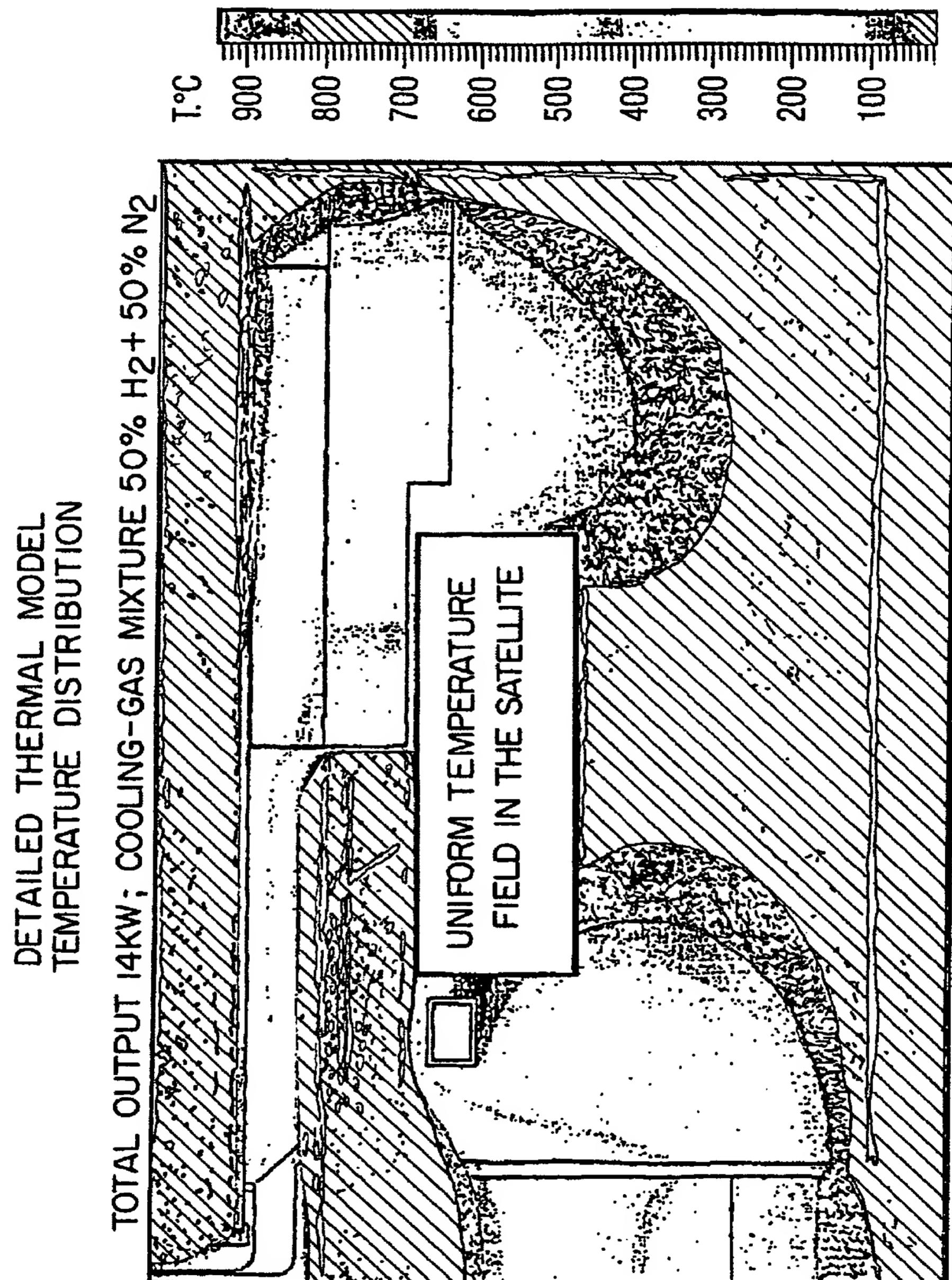


FIG. 3C

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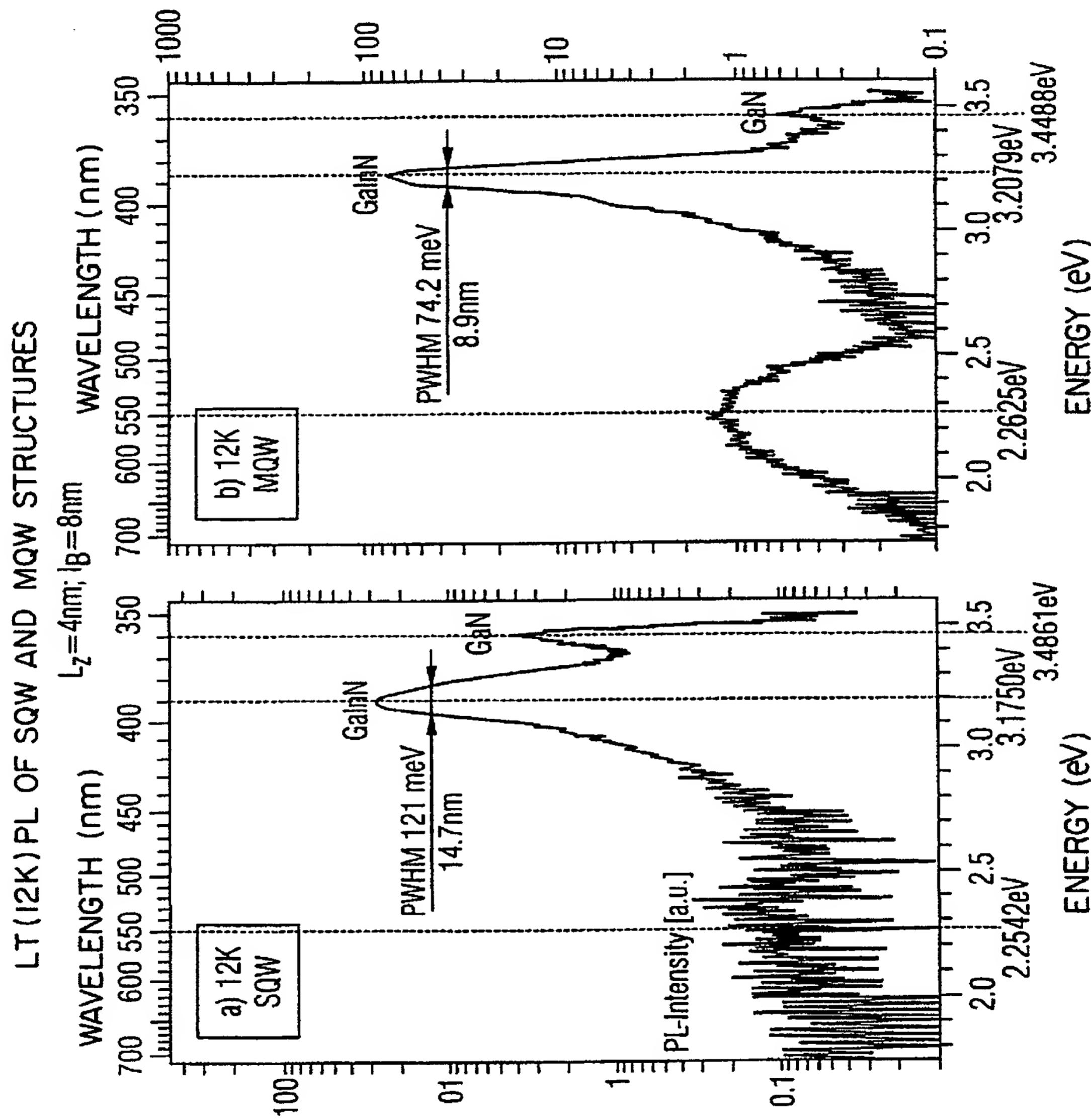
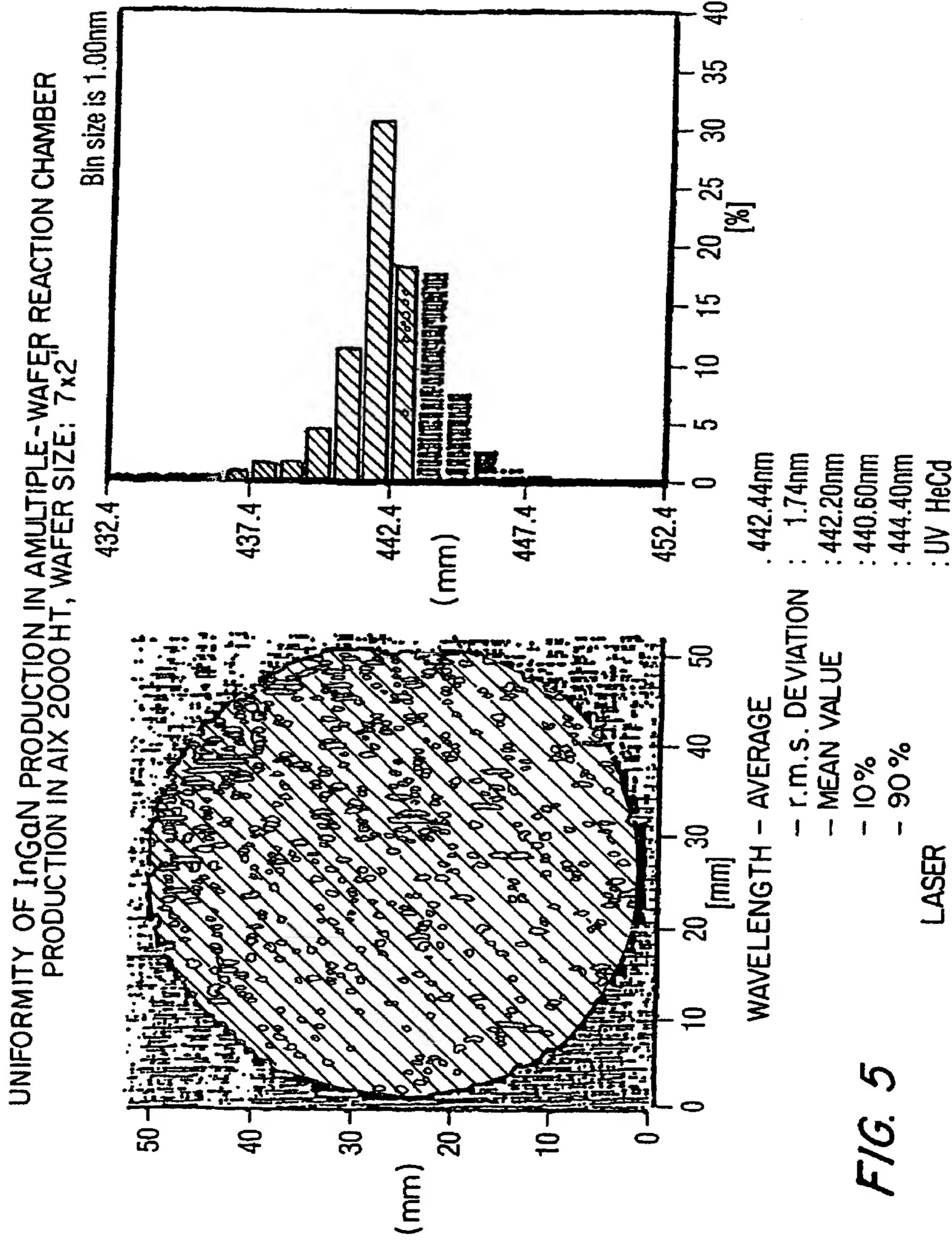
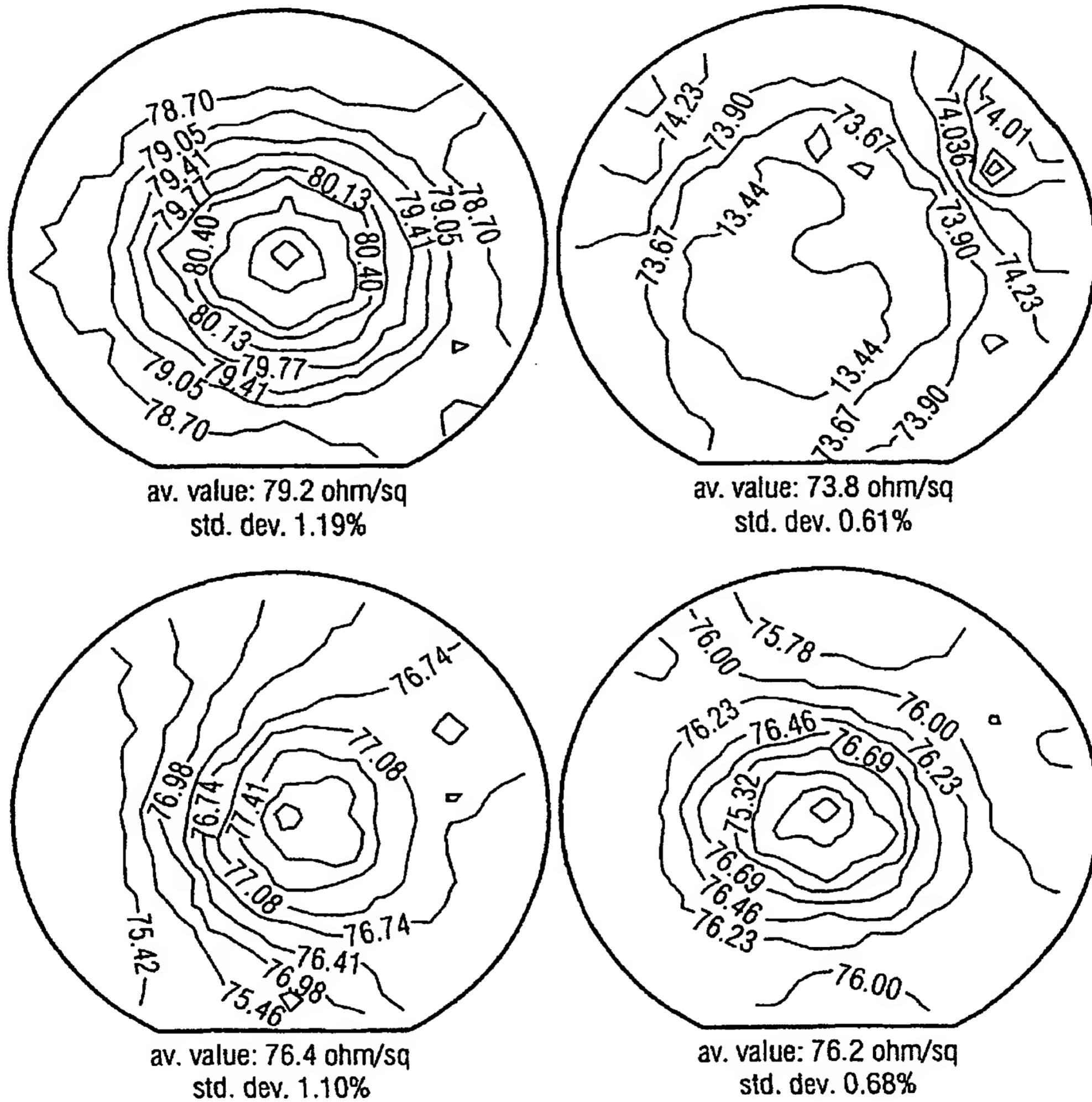


FIG. 4



WAFER TO WAFER HOMOGENEITY OF n - DOPED  
GaN/InGaN-DHS



WAFER TO WAFER r. m. s. DEVIATION: 2,7 %

FIG. 6

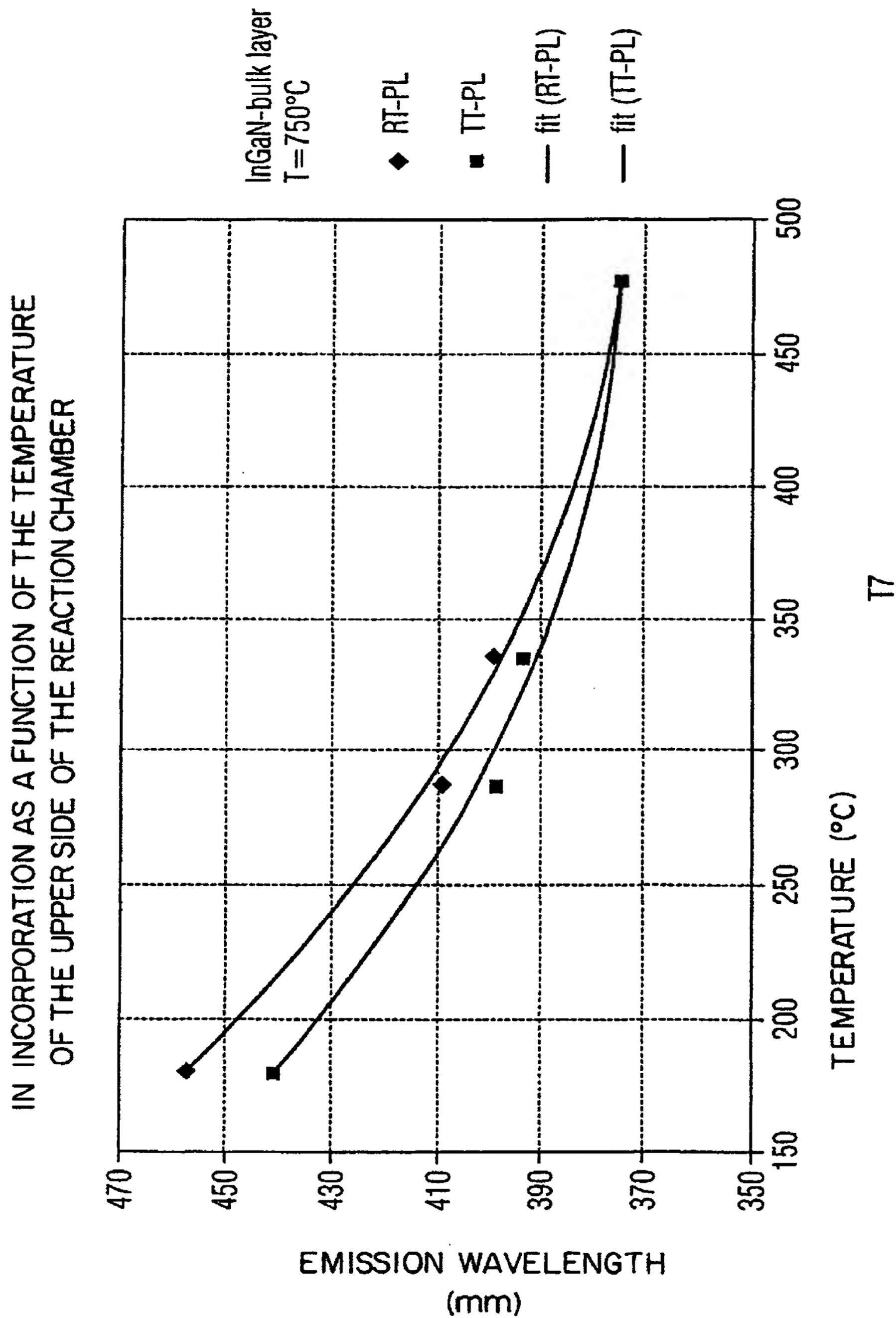


FIG. 7

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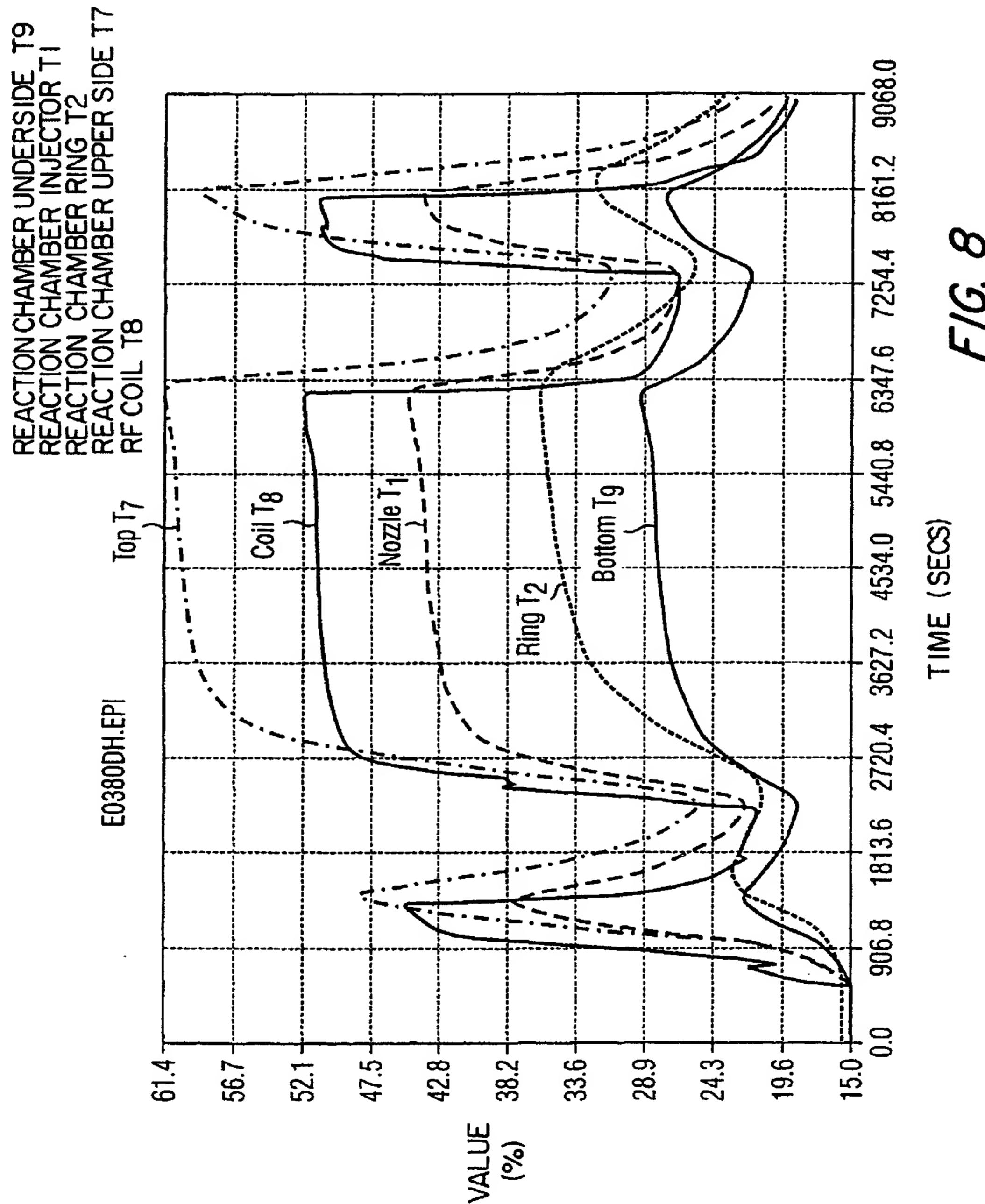


FIG. 8